



## N-Channel 30-V (D-S) MOSFET

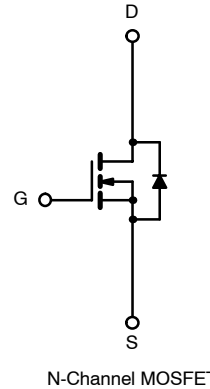
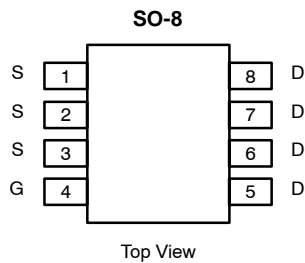
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
30	0.0045 @ V <sub>GS</sub> = 10 V	20
	0.0055 @ V <sub>GS</sub> = 4.5 V	19

### FEATURES

- TrenchFET® Power MOSFET
- Optimized for “Low Side” Synchronous Rectifier Operation
- 100% R<sub>g</sub> Tested

### APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



Ordering Information: Si4362DY  
Si4362DY-T1 (with Tape and Reel)  
Si4362DY—E3 (Lead Free)  
Si4362DY-T1—E3 (Lead Free with Tape and Reel)

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED) <sup>a</sup>			
Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	
Gate-Source Voltage	V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	20
		T <sub>A</sub> = 70 °C	15
Pulsed Drain Current (10 μs Pulse Width)	I <sub>DM</sub>	60	A
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.9	
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	3.5
		T <sub>A</sub> = 70 °C	2.2
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	

THERMAL RESISTANCE RATINGS <sup>a</sup>				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient	R <sub>thJA</sub>	29	35	°C/W
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	13	16	

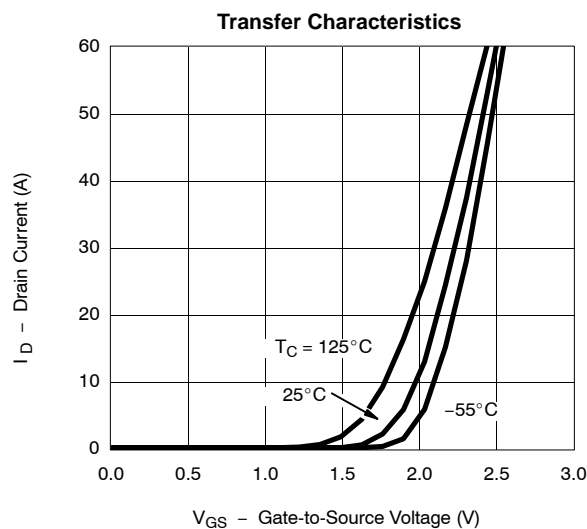
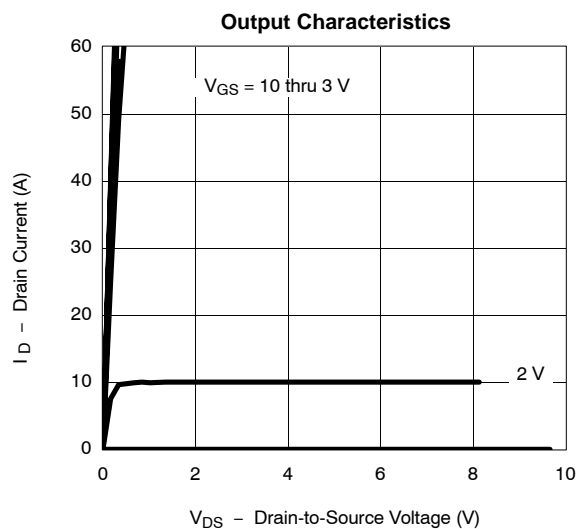
Notes  
a. Surface Mounted on 1" x 1" FR4 Board, t ≤ 10 sec

**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.6			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±12 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.0035	0.0045	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 19 A		0.0042	0.0055	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		90		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 2.9 A, V <sub>GS</sub> = 0 V		0.75	1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A		42	55	nC
Gate-Source Charge	Q <sub>gs</sub>			12.8		
Gate-Drain Charge	Q <sub>gd</sub>			7.7		
Gate Resistance	R <sub>G</sub>		0.5	1.3	2.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω		17	30	ns
Rise Time	t <sub>r</sub>			14	25	
Turn-Off Delay Time	t <sub>d(off)</sub>			158	230	
Fall Time	t <sub>f</sub>			43	65	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, di/dt = 100 A/μs		50	80	

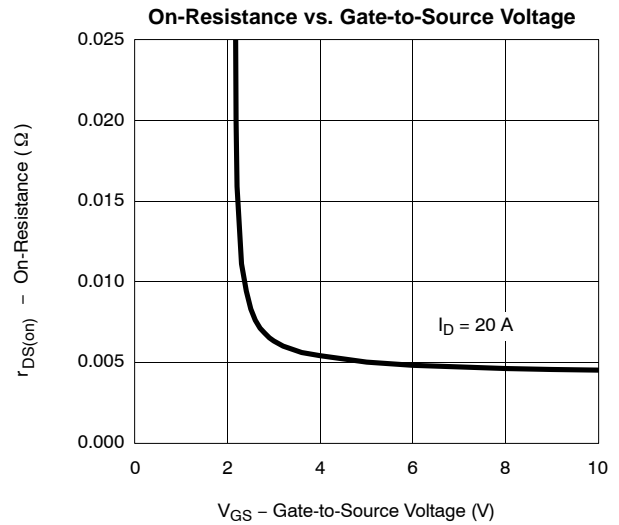
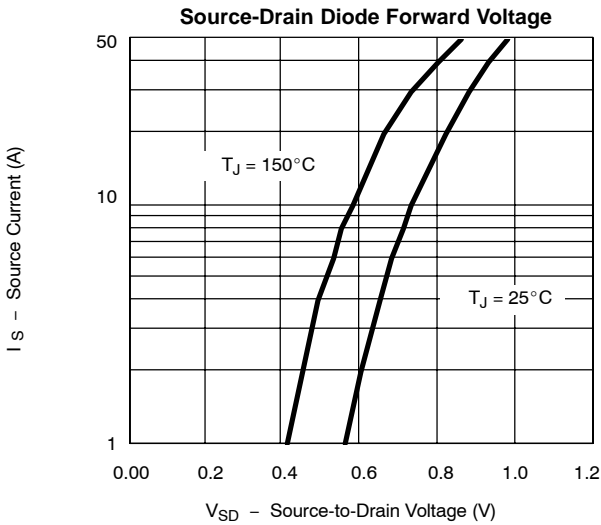
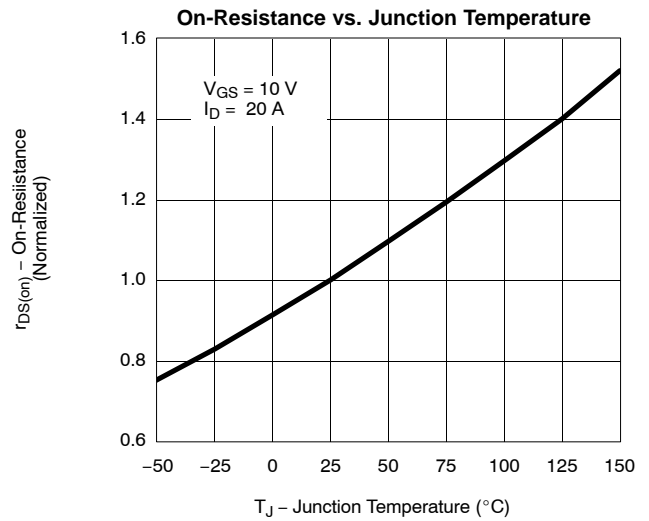
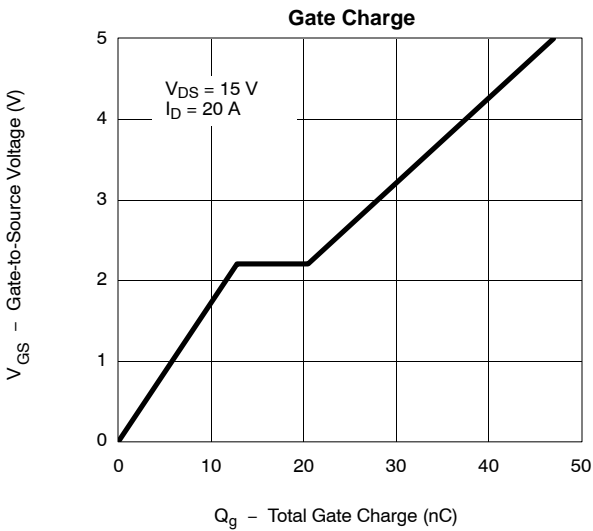
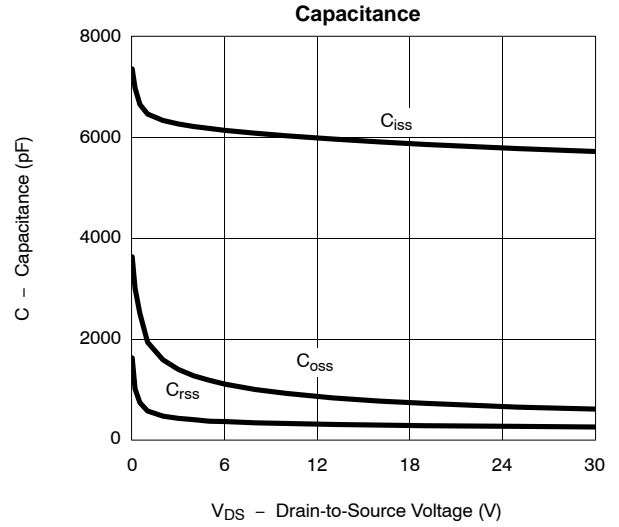
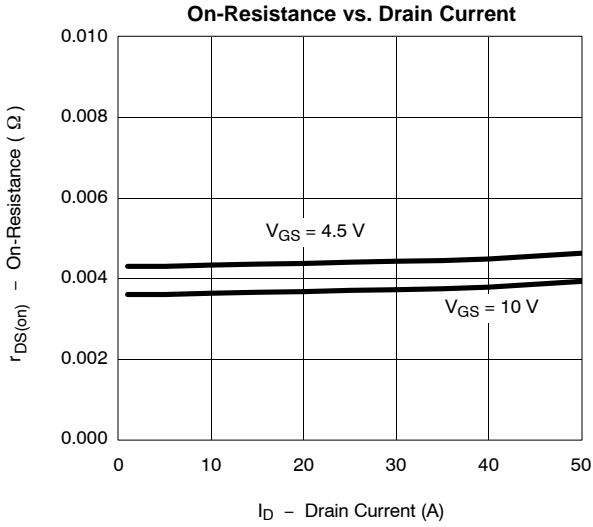
## Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



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